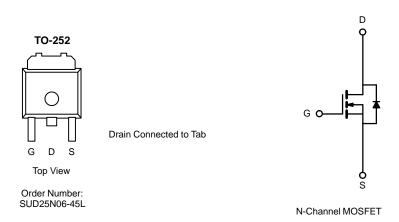


### **SUD25N06-45L** N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	
60	0.035 @ V <sub>GS</sub> = 10 V	25	
	$0.045 @ V_{GS} = 4.5 V$	22	



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = $25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	60	V	
Gate-Source Voltage		V <sub>GS</sub>	±20		
Continuous Drain Current (T. 175°C)	$T_{C} = 25^{\circ}C$		25		
Continuous Drain Current ( $T_J = 175^{\circ}C$ )	T <sub>C</sub> = 100°C		16		
Pulsed Drain Current		I <sub>DM</sub>	30	А	
Continuous Source Current (Diode Conduction)		۱ <sub>S</sub>	25		
Avalanche Current		I <sub>AR</sub>	25		
Repetitive Avalanche Energy (Duty Cycle $\leq$ 1%)	L = 0.1 mH	E <sub>AR</sub>	31	mJ	
Maximum Power Dissipation	$T_{C} = 25^{\circ}C$		50	w	
	$T_A = 25^{\circ}C$		2.5 <sup>a</sup>	VV	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	60	°C/W	
Maximum Junction-to-Case	R <sub>thJC</sub>	3.0		



**N-Channel** 

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Parameter	Symbol	Test Condition	Min	Тура	Max	Unit	
Static				•	•		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, $I_D$ = 250 $\mu$ A	60			v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0		3.0		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±20 V			±100	nA	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125^{\circ}\text{C}$			50		
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175^{\circ}\text{C}$			150		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10V$	20			A	
		$V_{GS} = 10$ V, $I_{D} = 12$ A		0.025	0.035	Ω	
Drain-Source On-State Resistance <sup>b</sup>		$V_{GS}$ = 10 V, $I_D$ = 12 A, $T_J$ = 125°C		0.045	0.063		
Drain-Source On-State Resistance	<sup>r</sup> DS(on)	$V_{GS}$ = 10 V, I <sub>D</sub> = 12 A, T <sub>J</sub> = 175°C		0.058	0.081		
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 12 \text{ A}$		0.036	0.045	1	
Forward Transconductance <sup>b</sup>	9fs	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 12 \text{ A}$	15	25		S	
Dynamic							
Input Capacitance	C <sub>iss</sub>			1320		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1 MHz		210			
Reverse Transfer Capacitance	C <sub>rss</sub>			56			
Total Gate Charge <sup>c</sup>	Qg			26	40	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS}$ = 30 V, $~V_{GS}$ = 10 V, $I_{D}$ = 25 A		7.5			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			4.5			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10	20	ns	
Rise Time <sup>c</sup>	tr	$V_{DD} = 30 \text{ V}, \text{ R}_{L} = 1.2 \Omega$ $I_{D} \cong 25 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{G} = 7.5 \Omega$		10	20		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 25 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{G}} = 7.5 \Omega$		31	45		
Fall Time <sup>c</sup>	t <sub>f</sub>			10	20		
Source-Drain Diode Ratings a	nd Characteristi	cs (T <sub>C</sub> = 25°C) <sup>a</sup>					
Pulsed Current	I <sub>SM</sub>				30	Α	
Diode Forward Voltage	V <sub>SD</sub>	$I_{F} = 25 \text{ A}, V_{GS} = 0 \text{ V}$			1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	L = 25 A di/dt 100 A/		60	90	ns	
Reverse Recovery Charge	Q <sub>rr</sub>	$I_{F} = 25 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		0.13	İ	μC	

Notes:

For design aid only; not subject to production testing. Pulse test; pulse width  $\leq 300 \ \mu$ s, duty cycle  $\leq 2\%$ . Independent of operating temperature. a.

b.

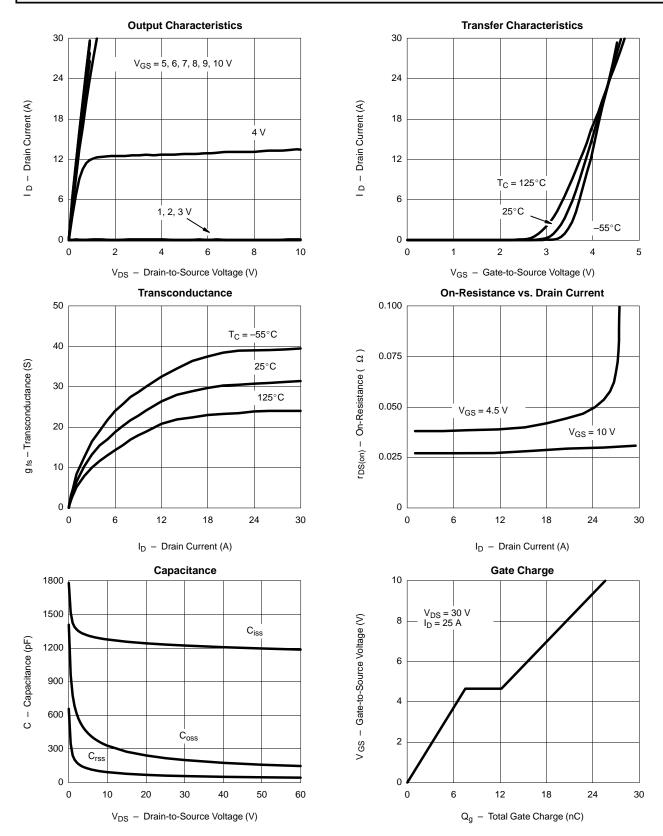
c.



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#### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

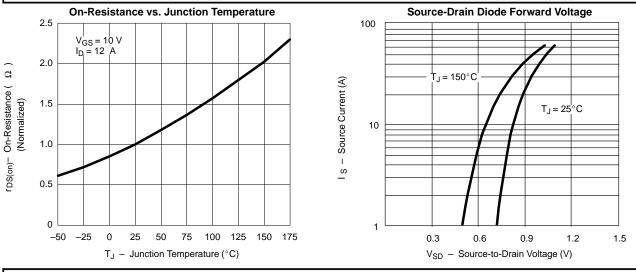




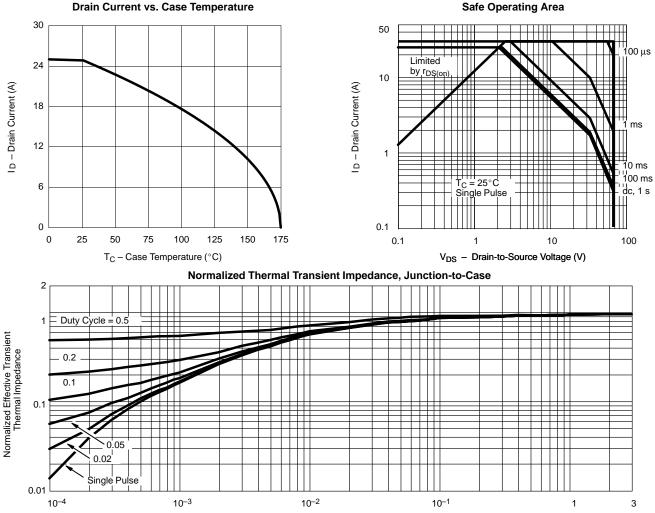
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#### **TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**



#### THERMAL RATINGS



Safe Operating Area



N-Channel

60 V (D-S) 175 °C MOSFET

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